

SANYO

No.199J

2SB544/2SD400

PNP/NPN Epitaxial Planar Silicon Transistors

Low-Frequency Power Amp,
Electronic Governor Applications

(): 2SB544

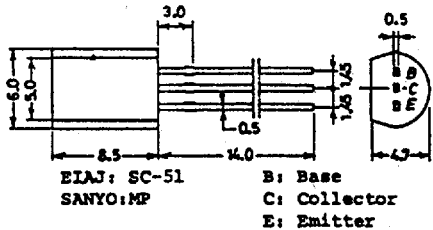
Absolute Maximum Ratings at Ta=25°C			unit
Collector to Base Voltage	V _{CBO}	(-)25	V
Collector to Emitter Voltage	V _{CEO}	(-)25	V
Emitter to Base Voltage	V _{EBO}	(-)5	V
Collector Current	I _C	(-)1	A
Collector Current(Pulse)	I _{CP}	(-)2	A
Collector Dissipation	P _C	900	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} =(-)20V, I _E =0			(-)1.0	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)4V, I _C =0			(-)1.0	μA
DC Current Gain	h _{FE} (1)	V _{CE} =(-)2V, I _C =(-)50mA	60※		560※	
	h _{FE} (2)	V _{CE} =(-)2V, I _C =(-)1A	30			
Gain-Bandwidth Product	f _T	V _{CE} =(-)10V, I _C =(-)50mA		180		MHz
Output Capacitance	c _{ob}	V _{CB} =(-)10V, f=1MHz		(25)		pF
				15		
C-E Saturation Voltage	V _{CE(sat)}	I _C =(-)500mA, I _B =(-)50mA		(- 0.15)	(- 0.7)	V
				0.1	0.3	
B-E Saturation Voltage	V _{BE(sat)}	I _C =(-)500mA, I _B =(-)50mA		(-)0.85	(-)1.2	V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C =(-)10μA, I _E =0	(-)25			V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C =(-)1mA, R _{BE} = ∞	(-)25			V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E =(-)10μA, I _C =0	(-)5			V

※ : The 2SB544/2SD400 are classified by 50mA h_{FE} as follows :

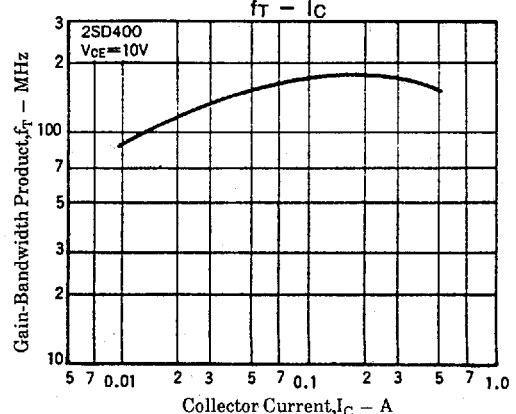
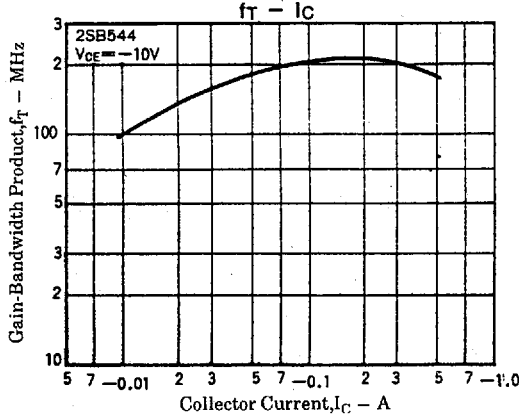
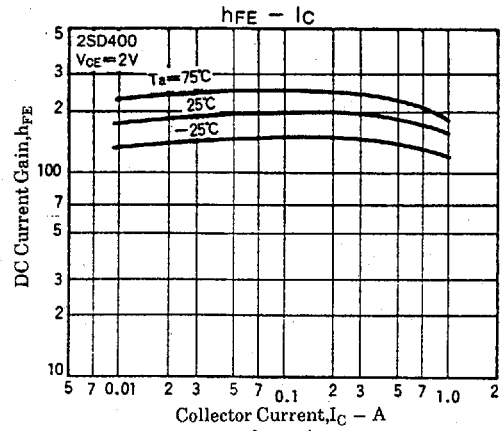
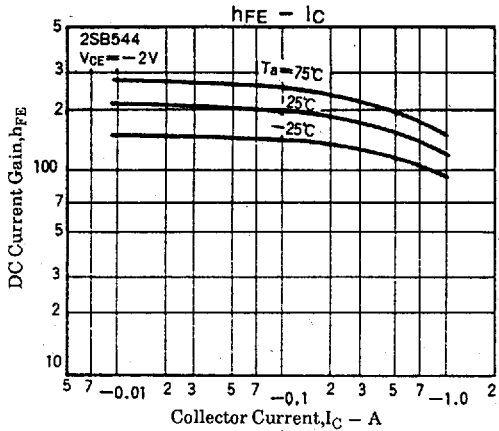
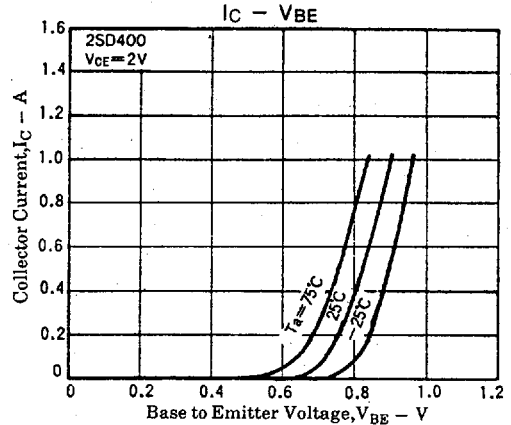
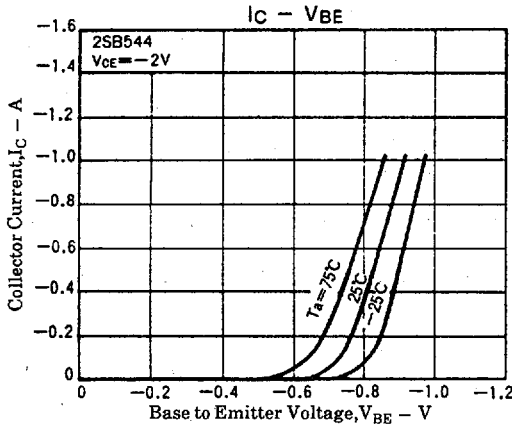
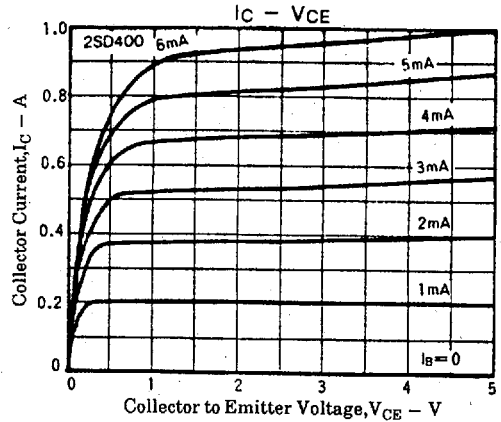
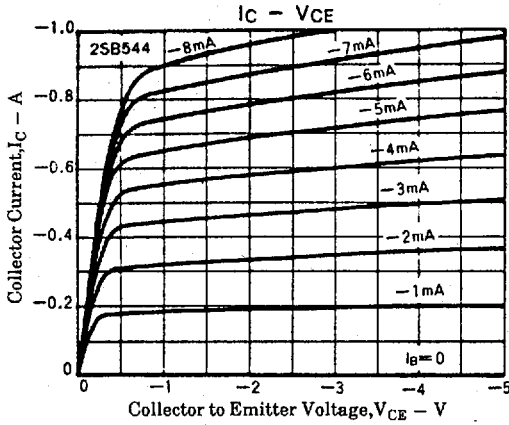
60	D	120	100	E	200	160	F	320	280	G	560
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Case Outline 2006A
(unit : mm)

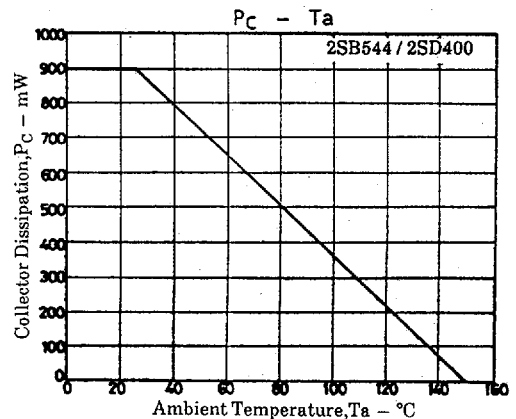
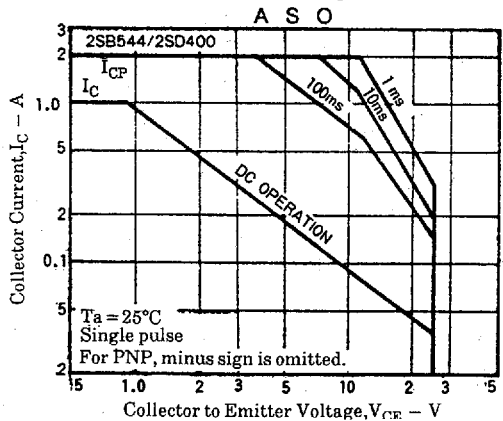
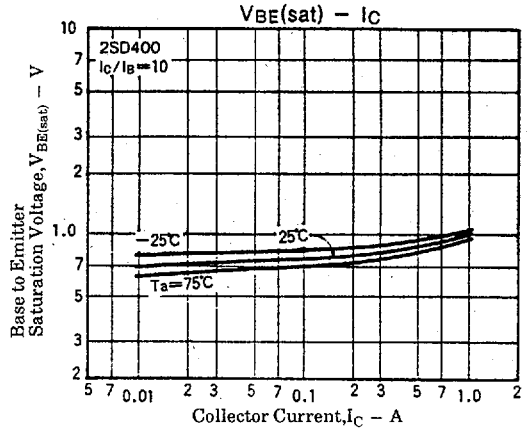
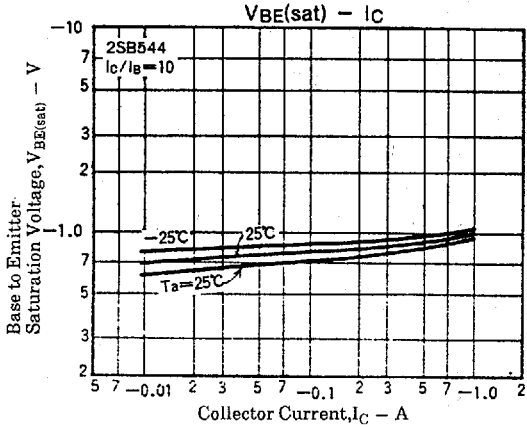
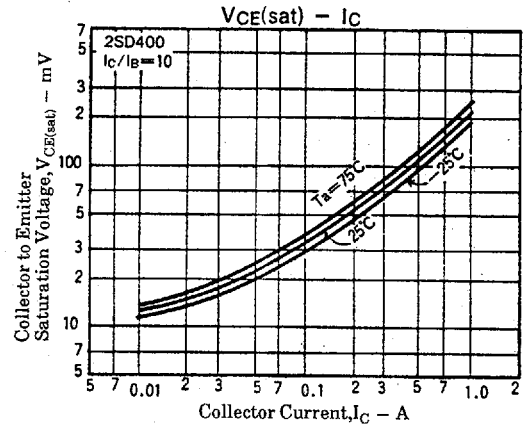
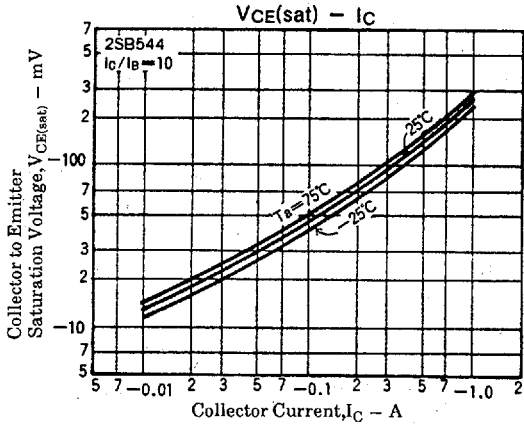
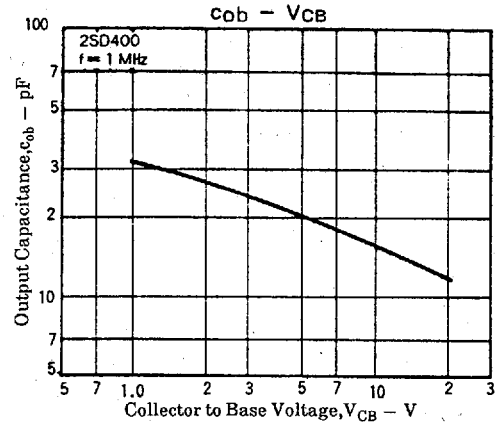
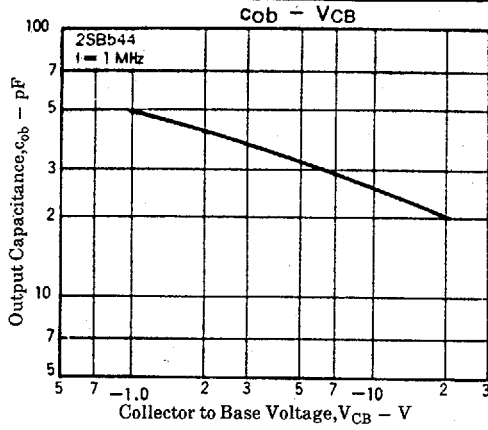


Specifications and information herein are subject to change without notice.

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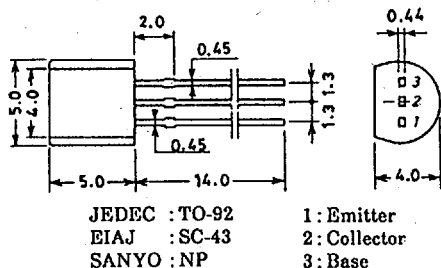
2SB544/2SD400



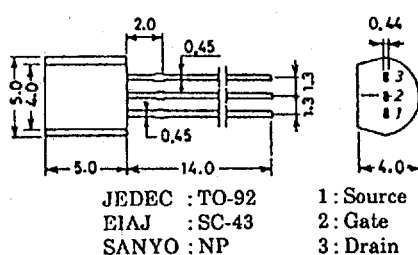
CASE OUTLINES OF LEAD FORMED SMALL SIGNAL TRANSISTORS

- All of Sanyo lead formed small signal transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

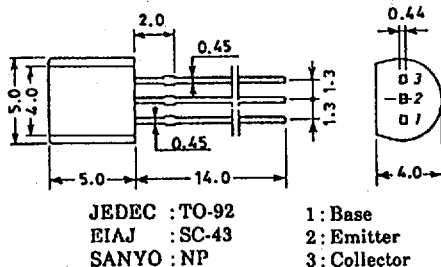
Case Outline 2003A/2003B (unit : mm)



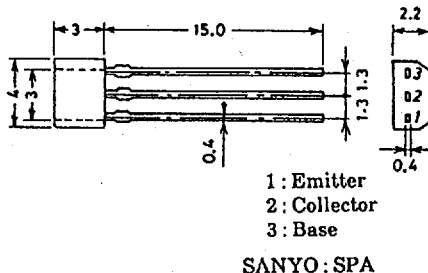
Case Outline 2019A/2019B (unit : mm)



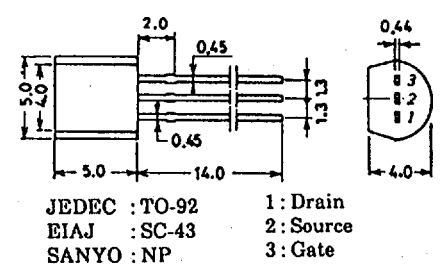
Case Outline 2004A (unit : mm)



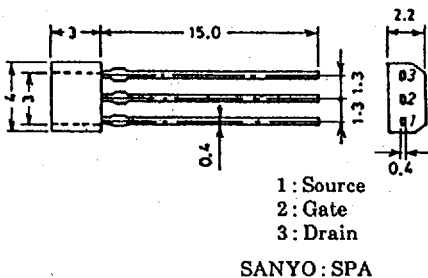
Case Outline 2033 (unit : mm)



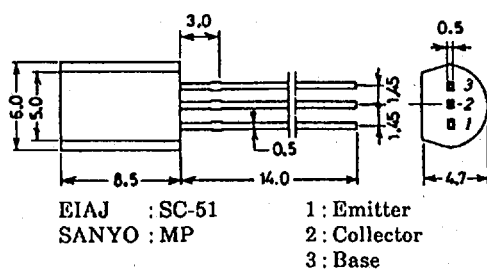
Case Outline 2005A (unit : mm)



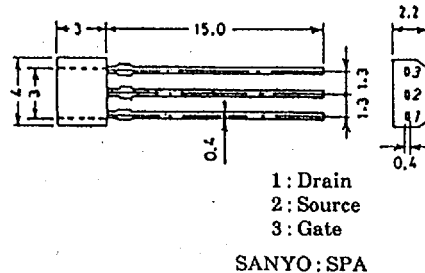
Case Outline 2034/2034A (unit : mm)



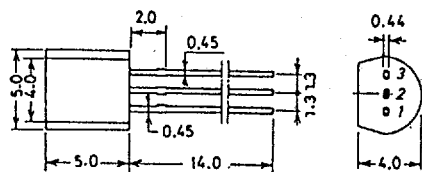
Case Outline 2006A (unit : mm)



Case Outline 2040 (unit : mm)



Case Outline 2061 (unit : mm)



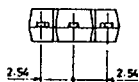
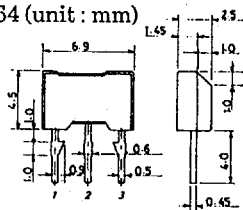
JEDEC : TO-92

EIAJ : SC-43

SANYO : NP

- 1: Emitter
- 2: Base
- 3: Collector

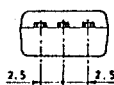
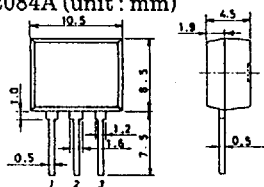
Case Outline 2064 (unit : mm)



- 1: Emitter
- 2: Collector
- 3: Base

SANYO : NMP

Case Outline 2084A (unit : mm)



- 1: Emitter
- 2: Collector
- 3: Base

SANYO : FLIP